

# EL2228

Data Sheet

### July 29, 2002

# **Dual Low Noise Amplifier**



The EL2228 is a dual, low-noise amplifier, ideally suited to filtering applications in ADSL and HDSLII

designs. It features low noise specification of just 4.9nV/ $\sqrt{Hz}$  and 1.2pA/ $\sqrt{Hz}$ , making it ideal for processing low voltage waveforms.

The EL2228 has a -3dB bandwidth of 80MHz and is gain-of-1 stable. It also affords minimal power dissipation with a supply current of just 4.5mA per amplifier. The amplifier can be powered from supplies ranging from  $\pm 2.5V$  to  $\pm 12V$ .

The EL2228 is available in a space saving 8-pin MSOP package as well as the industry-standard 8-pin SO. It is specified for operation over the -40°C to +85°C temperature range.

## **Ordering Information**

PART NUMBER	PACKAGE	TAPE & REEL	PKG. NO.
EL2228CY	8-Pin MSOP	-	MDP0043
EL2228CY-T13	8-Pin MSOP	13"	MDP0043
EL2228CY-T7	8-Pin MSOP	7"	MDP0043
EL2228CS	8-Pin SO	-	MDP0027
EL2228CS-T13	8-Pin SO	13"	MDP0027
EL2228CS-T7	8-Pin SO	7"	MDP0027

#### Features

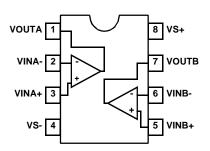
- Voltage noise of only 4.9nV/√Hz
- Current noise of only 1.2pA/√Hz
- Bandwidth (-3dB) of 80MHz -@ A<sub>V</sub> = +1
- Gain-of-1 stable
- Just 4.5mA per amplifier
- 8-pin MSOP package
- ±2.5V to ±12V operation

### Applications

- ADSL filters
- HDSLII filters
- Ultrasound input amplifiers
- Wideband instrumentation
- · Communications equipment
- Wideband sensors

#### Pinout

EL2228 (8-PIN SO, MSOP) TOP VIEW



#### Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

Supply Voltage between V <sub>S</sub> + and V <sub>S</sub> +28V
Input Voltage
Maximum Continuous Output Current
ESD Voltage2kV

Maximum Die Temperature	+150°C
Storage Temperature	65°C to +150°C
Power Dissipation	See Curves
Operating Temperature	-40°C to +85°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE: All parameters having Min/Max specifications are guaranteed. Typ values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore:  $T_J = T_C = T_A$ 

 $\label{eq:constraint} \textbf{Electrical Specifications} \quad V_S \texttt{+} = \texttt{+}12 V, \ V_S \texttt{-} = \texttt{-}12 V, \ \mathsf{R}_L = \texttt{500} \Omega \ \text{and} \ \mathsf{C}_L = \texttt{3pF} \ \text{to} \ \texttt{0V}, \ \mathsf{R}_F = \texttt{420} \Omega \ \text{and} \ \mathsf{T}_A = \texttt{25}^\circ C \ \text{unless otherwise specified}.$ 

PARAMETER	DESCRIPTION	CONDITIONS	MIN	ТҮР	MAX	UNIT
INPUT CHARA	CTERISTICS					
V <sub>OS</sub>	Input Offset Voltage	$V_{CM} = 0V$		0.2	3	mV
TCV <sub>OS</sub>	Average Offset Voltage Drift	Measured over operating temperature range		-4		µV/°C
IB	Input Bias Current	$V_{CM} = 0V$	-9	-4.5	-1	μA
R <sub>IN</sub>	Input Impedance			8		MΩ
C <sub>IN</sub>	Input Capacitance			1		pF
CMIR	Common-Mode Input Range	-11.8			+10.4	V
CMRR	Common-Mode Rejection Ratio	for V <sub>IN</sub> from -11.8V to +10.4V	60	90		dB
		for V <sub>IN</sub> from -10V to +10V	60	75		dB
A <sub>VOL</sub>	Open-Loop Gain	$-5V \le V_{OUT} \le 5V$	60	75		dB
e <sub>N</sub>	Voltage Noise	f = 100kHz		4.9		nV/√Hz
i <sub>N</sub>	Current Noise	f = 100kHz		1.2		pA/√Hz
OUTPUT CHAR	ACTERISTICS					
V <sub>OL</sub>	Output Swing Low	$R_L = 500\Omega$		-10.3	-10	V
		R <sub>L</sub> = 250Ω		-9.5	-9	V
V <sub>OH</sub>	Output Swing High	$R_L = 500\Omega$	10	10.3		V
		$R_L = 250\Omega$	9.5	10		V
I <sub>SC</sub>	Short Circuit Current	$R_L = 10\Omega$	140	180		mA
POWER SUPPL	Y PERFORMANCE					
PSRR	Power Supply Rejection Ratio	$V_S$ is moved from ±10.8V to ±13.2V	65	83		dB
IS	Supply Current (per Amplifier)	No load	4	5	6	mA
DYNAMIC PER	FORMANCE					
SR	Slew Rate (Note 1)	±2.5V square wave, measured 25%-75%	44	65		V/µs
t <sub>S</sub>	Settling to +0.1% ( $A_V = +1$ )	$(A_V = +1), V_O = 2V \text{ step}$		50		ns
BW	-3dB Bandwidth			80		MHz
HD2	2nd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, A_V = 2$		-86		dBc
		$f = 1MHz, V_O = 2V_{P-P}, R_L = 150\Omega, A_V = 2$		-79		dBc
HD3	3rd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, A_V = 2$		-93		dBc
		f = 1MHz, $V_O$ = 2 $V_{P-P}$ , $R_L$ = 150Ω, $A_V$ = 2		-70		dBc

NOTE:

1. Slew rate is measured on rising and falling edges

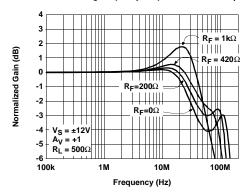
PARAMETER	DESCRIPTION	CONDITIONS	MIN	TYP	MAX	UNIT
INPUT CHARAG	CTERISTICS					
V <sub>OS</sub>	Input Offset Voltage	$V_{CM} = 0V$		0.6	3	mV
TCV <sub>OS</sub>	Average Offset Voltage Drift	Measured over operating temperature range		4.9		μV/°C
IB	Input Bias Current	$V_{CM} = 0V$	-9	-4.5	-1	μA
R <sub>IN</sub>	Input Impedance			6		MΩ
C <sub>IN</sub>	Input Capacitance			1.2		pF
CMIR	Common-Mode Input Range		-4.7		+3.4	V
CMRR	Common-Mode Rejection Ratio	for V <sub>IN</sub> from -4.7V to +3.4V	60	90		dB
		for $V_{IN}$ from -2V to +2V				dB
A <sub>VOL</sub>	Open-Loop Gain	$-2.5V \le V_{OUT} \le 2.5V$	60	72		dB
e <sub>N</sub>	Voltage Noise	f = 100kHz		4.7		nV/√Hz
i <sub>N</sub>	Current Noise	f = 100kHz		1.2		pA/√Hz
OUTPUT CHAR	ACTERISTICS					
V <sub>OL</sub>	Output Swing Low	$R_L = 500\Omega$		-3.8	-3.5	V
		$R_L = 250\Omega$		-3.7	-3.5	V
V <sub>OH</sub>	Output Swing High	$R_L = 500\Omega$	3.5	3.7		V
		$R_L = 250\Omega$	3.5	3.6		V
I <sub>SC</sub>	Short Circuit Current	$R_L = 10\Omega$	60	100		mA
POWER SUPPL	YPERFORMANCE					
PSRR	Power Supply Rejection Ratio	$V_{\mbox{S}}$ is moved from ±4.5V to ±5.5V	65	83		dB
IS	Supply Current (Per Amplifier)	No load	3.5	4.5	5.5	mA
DYNAMIC PER	FORMANCE					
SR	Slew Rate (Note 1)	±2.5V square wave, measured 25%-75%	35	50		V/µs
ts	Settling to +0.1% ( $A_V = +1$ )	$(A_V = +1), V_O = 2V \text{ step}$		50		ns
BW	-3dB Bandwidth			75		MHz
HD2	2nd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, A_V = 2$		-90		dBc
		$f = 1MHz, V_O = 2V_{P-P}, R_L = 150\Omega, A_V = 2$		-71		dBc
HD3	3rd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, A_V = 2$		-99		dBc
		f = 1MHz, $V_{O}$ = 2 $V_{P-P}$ , $R_{L}$ = 150Ω, $A_{V}$ = 2		-69		dBc

NOTE:

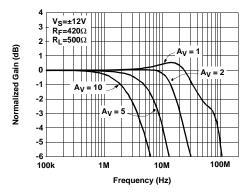
1. Slew rate is measured on rising and falling edges

## Typical Performance Curves

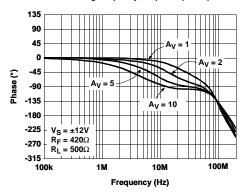
Non-Inverting Frequency Response for Various R<sub>F</sub>

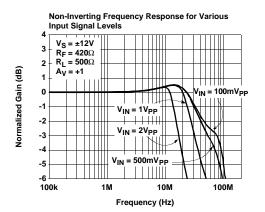




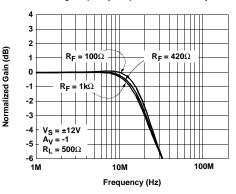


Non-Inverting Frequency Response (Phase)

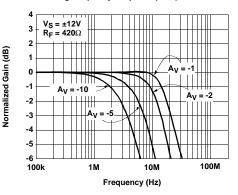




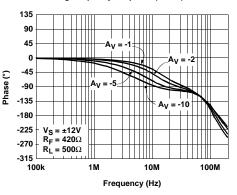
Inverting Frequency Response for Various RF



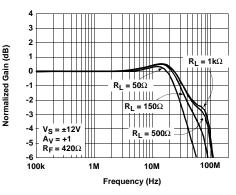
Inverting Frequency Response (Gain)



Inverting Frequency Response (Phase)

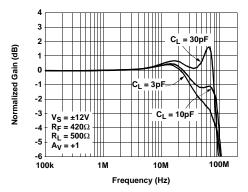


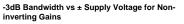
Non-Inverting Frequency Response for Various RL

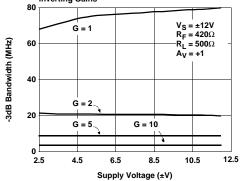


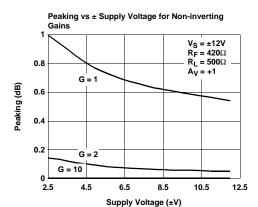
# Typical Performance Curves (Continued)

Non-Inverting Frequency Response for Various CL

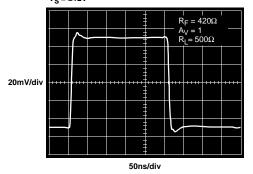


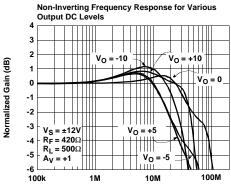




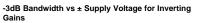


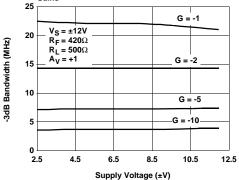




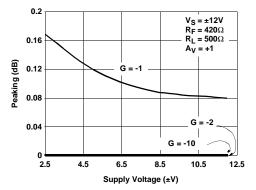


Frequency (Hz)

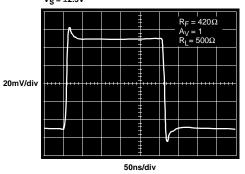




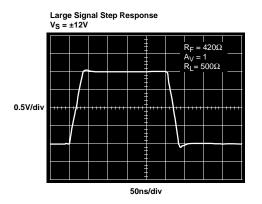
Peaking vs ± Supply Voltage for Inverting Gains

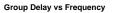


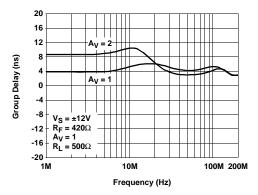


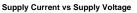


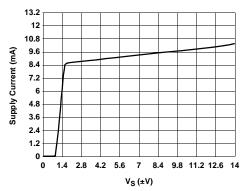




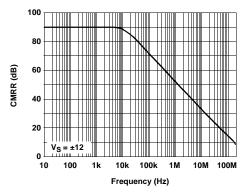


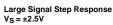


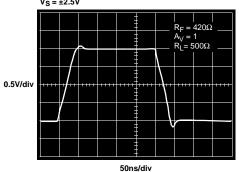


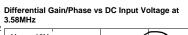


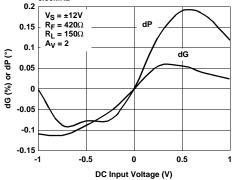




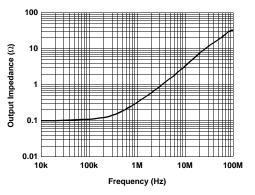




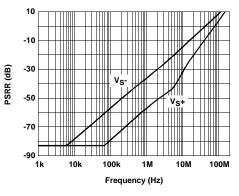




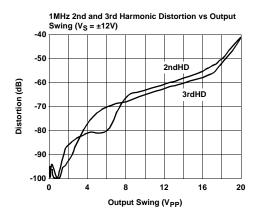
**Closed Loop Output Impedance vs Frequency** 

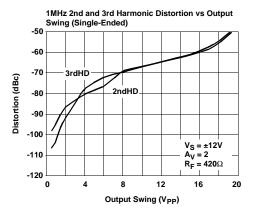




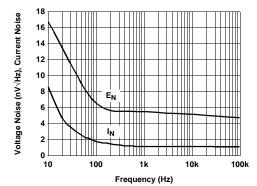


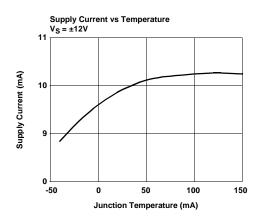


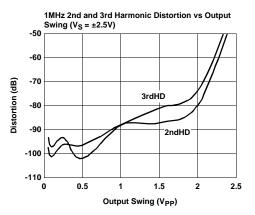




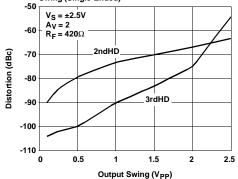




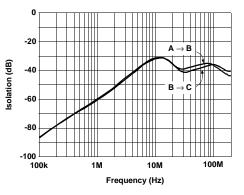


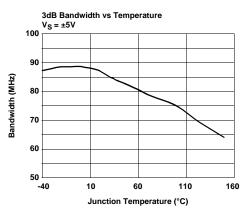




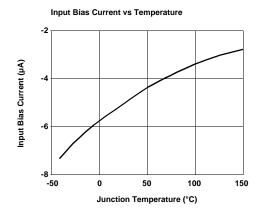


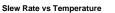
**Channel to Channel Isolation vs Frequency** 

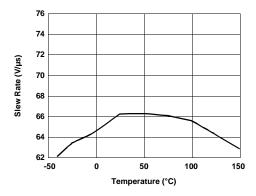


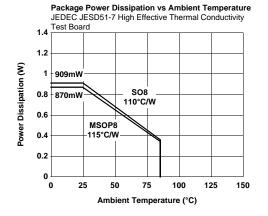


# Typical Performance Curves (Continued)



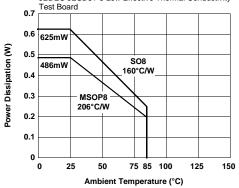






2 Input Offset Voltage (mV) 1 0 -1 -2 -50 50 100 150 0 Junction Temperature (°C)

Package Power Dissipation vs Ambient Temperature JEDEC JESD51-3 Low Effective Thermal Conductivity Test Board



#### Input Offset Voltage vs Temperature

# **Pin Descriptions**

8-PIN MSOP	8-PIN SO	PIN NAME	PIN FUNCTION	EQUIVALENT CIRCUIT
1	1	V <sub>OUT</sub> A	Output	
2	2	V <sub>IN</sub> A-	Input	$V_{IN}$ + $V_{IN}$ - $V_{IN}$ - V <sub>S</sub> - CIRCUIT 2
3	3	V <sub>IN</sub> A+	Input	Reference Circuit 2
4	4	VS-	Supply	
5	5	V <sub>IN</sub> B+	Input	
6	6	V <sub>IN</sub> B-	Input	Reference Circuit 2
7	7	V <sub>OUT</sub> B	Output	Reference Circuit 1
8	8	V <sub>S</sub> +	Supply	

# Applications Information

## **Product Description**

The EL2228 is a dual voltage feedback operational amplifier designed especially for DMT ADSL and other applications requiring very low voltage and current noise. It also features low distortion while drawing moderately low supply current and is built on Elantec's proprietary high-speed complementary bipolar process. The EL2228 uses a classical voltage-feedback topology which allows them to be used in a variety of applications where current-feedback amplifiers are not appropriate because of restrictions placed upon the feedback element used with the amplifier. The conventional topology of the EL2228 allows, for example, a capacitor to be placed in the feedback path, making it an excellent choice for applications such as active filters, sample-and-holds, or integrators.

## Single-Supply Operation

The EL2228 was designed to have a wide input and output voltage range. This design also makes the EL2228 an

excellent choice for single-supply operation. Using a single positive supply, the lower input voltage range is within 300mV of ground ( $R_L = 500\Omega$ ), and the lower output voltage range is within 875mV of ground. Upper input voltage range reaches 3.6V, and output voltage range reaches 3.8V with a 5V supply and  $R_L = 500\Omega$ . This results in a 2.625V output swing on a single 5V supply. This wide output voltage range also allows single-supply operation with a supply voltage as high as 28V.

#### Gain-Bandwidth Product and the -3dB Bandwidth

The EL2228 has a gain-bandwidth product of 40MHz while using only 5mA of supply current per amplifier. For gains greater than 1, their closed-loop -3dB bandwidth is approximately equal to the gain-bandwidth product divided by the noise gain of the circuit. For gains of 1, higher-order poles in the amplifiers' transfer function contribute to even higher closed loop bandwidths. For example, the EL2228 have a -3dB bandwidth of 80MHz at a gain of 1, dropping to 9MHz at a gain of 5. It is important to note that the EL2228 is designed so that this "extra" bandwidth in low-gain application does not come at the expense of stability. As seen in the typical performance curves, the EL2228 in a gain of only 1 exhibited 0.5dB of peaking with a  $500\Omega$  load.

#### **Output Drive Capability**

The EL2228 is designed to drive a low impedance load. It can easily drive  $6V_{P-P}$  signal into a  $500\Omega$  load. This high output drive capability makes the EL2228 an ideal choice for RF, IF, and video applications. Furthermore, the EL2228 is current-limited at the output, allowing it to withstand momentary short to ground. However, the power dissipation with output-shorted cannot exceed the power dissipation capability of the package.

#### **Driving Cables and Capacitive Loads**

Although the EL2228 is designed to drive low impedance load, capacitive loads will decreases the amplifier's phase margin. As shown in the performance curves, capacitive load can result in peaking, overshoot and possible oscillation. For optimum AC performance, capacitive loads should be reduced as much as possible or isolated with a series resistor between 5 $\Omega$  to 20 $\Omega$ . When driving coaxial cables, double termination is always recommended for reflection-free performance. When properly terminated, the capacitance of the coaxial cable will not add to the capacitive load seen by the amplifier.

#### **Power Dissipation**

With the wide power supply range and large output drive capability of the EL2228, it is possible to exceed the 150°C maximum junction temperatures under certain load and power-supply conditions. It is therefore important to calculate the maximum junction temperature ( $T_{JMAX}$ ) for all applications to determine if power supply voltages, load conditions, or package type need to be modified for the EL2228 to remain in the safe operating area. These parameters are related as follows:

$$T_{JMAX} = T_{MAX} + (\theta_{JA} x P D_{MAXTOTAL})$$

where:

- P<sub>DMAXTOTAL</sub> is the sum of the maximum power dissipation of each amplifier in the package (PD<sub>MAX</sub>)
- PD<sub>MAX</sub> for each amplifier can be calculated as follows:

$$PD_{MAX} = 2^*V_S \times I_{SMAX} + (V_S - V_{OUTMAX}) \times \frac{V_{OUTMAX}}{R_L}$$

#### where:

- T<sub>MAX</sub> = Maximum ambient temperature
- θ<sub>JA</sub> = Thermal resistance of the package
- PD<sub>MAX</sub> = Maximum power dissipation of 1 amplifier
- V<sub>S</sub> = Supply voltage
- I<sub>MAX</sub> = Maximum supply current of 1 amplifier
- V<sub>OUTMAX</sub> = Maximum output voltage swing of the application
- R<sub>I</sub> = Load resistance

# Power Supply Bypassing And Printed Circuit Board Layout

As with any high frequency devices, good printed circuit board layout is essential for optimum performance. Ground plane construction is highly recommended. Pin lengths should be kept as short as possible. The power supply pins must be closely bypassed to reduce the risk of oscillation. The combination of a 4.7 $\mu$ F tantalum capacitor in parallel with 0.1 $\mu$ F ceramic capacitor has been proven to work well when placed at each supply pin. For single supply operation, where pin 4 (V<sub>S</sub>-) is connected to the ground plane, a single 4.7 $\mu$ F tantalum capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor across pin 8 (V<sub>S</sub>+).

For good AC performance, parasitic capacitance should be kept to a minimum. Ground plane construction again should be used. Small chip resistors are recommended to minimize series inductance. Use of sockets should be avoided since they add parasitic inductance and capacitance which will result in additional peaking and overshoot.

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